

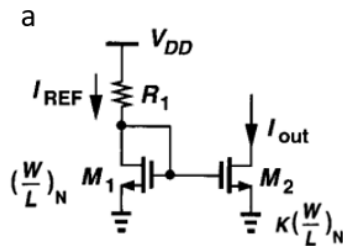
Tutorial 9 solutions

EE204: Analog Circuits

Dept of Electrical Engineering, IITB
Autumn Semester 2023

Q1.

A Derive expressions for **I_{out}** in the following 3 cases



Since V_{GS} of M1 is equal to M2, I_{out}=K*I_{ref}

$$V_{D1} = V_{G1} = V_{dd} - I_{ref}R_1 = \sqrt{\frac{2I_{ref}}{\frac{\mu_n C_{ox} W}{L}}} + V_{th}$$

Above equation gives a quadratic equation in I_{ref}, solving for I_{ref} gives

$$I_{ref} = \frac{V_{dd} - V_{th}}{R_1} + \frac{1}{\frac{\mu_n C_{ox} W}{L} R_1^2} \left(1 \pm \sqrt{1 + 2(V_{dd} - V_{th}) R_1 \frac{\mu_n C_{ox} W}{L}} \right)$$

The I_{ref} with Positive sqrt term is discarded as the Drop across Mosfet falls below V_{th}

So

$$I_{ref} = \frac{V_{dd} - V_{th}}{R_1} + \frac{1}{\frac{\mu_n C_{ox} W}{L} R_1^2} \left(1 - \sqrt{1 + 2(V_{dd} - V_{th}) R_1 \frac{\mu_n C_{ox} W}{L}} \right)$$

$$I_{out} = K * I_{ref} = \frac{K(V_{dd} - V_{th})}{R_1} + \frac{K}{\frac{\mu_n C_{ox} W}{L} R_1^2} \left(1 - \sqrt{1 + 2(V_{dd} - V_{th}) R_1 \frac{\mu_n C_{ox} W}{L}} \right)$$

B Derive expressions for I_{out}

From PMOS current mirror, $V_{GS4}=V_{GS3}$ so $I_{ref}=I_{out}$

Let $I_{ref}=I_{out}=I$

$V_{G1}=V_{G2}$

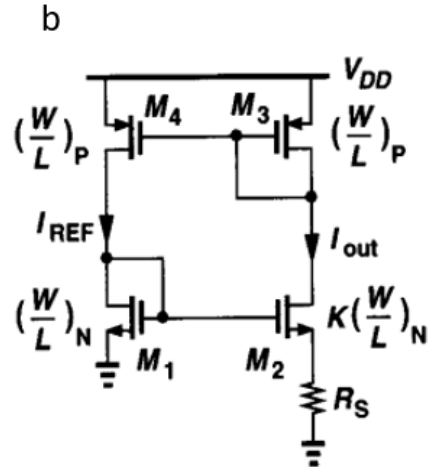
$$\sqrt{\frac{2I}{K_n}} + V_{th1} + V_{s1} = \sqrt{\frac{2I}{K \cdot K_n}} + V_{th2} + V_{s2}$$

$V_{th1}=V_{th2}$, $V_{s1}=0$, $V_{s2}=IR_s$

$$\sqrt{\frac{2I}{K_n}} = \sqrt{\frac{2I}{K \cdot K_n}} + IR_s$$

$$\sqrt{\frac{2}{K_n}} \left(1 - \frac{1}{\sqrt{K}}\right) = \sqrt{I} R_s$$

$$I = \frac{2}{K_n R_s^2} \left(1 - \frac{1}{\sqrt{K}}\right)^2$$



C Derive expressions for I_{out}

From PMOS current mirror, $V_{GS4}=V_{GS3}$ so $I_{ref}=I_{out}$

Let $I_{ref}=I_{out}=I$

$V_{G1}=V_{G2}+IR_s$

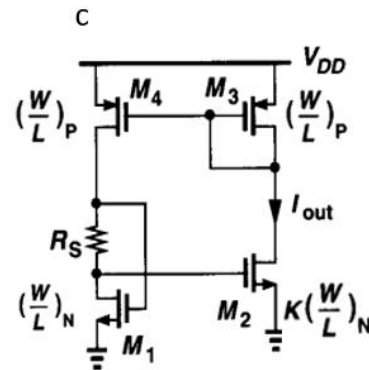
$$\sqrt{\frac{2I}{K_n}} + V_{th1} + V_{s1} = \sqrt{\frac{2I}{K \cdot K_n}} + V_{th2} + V_{s2} + IR_s$$

$V_{th1}=V_{th2}$, $V_{s1}=V_{s2}=0$

$$\sqrt{\frac{2I}{K_n}} = \sqrt{\frac{2I}{K \cdot K_n}} + IR_s$$

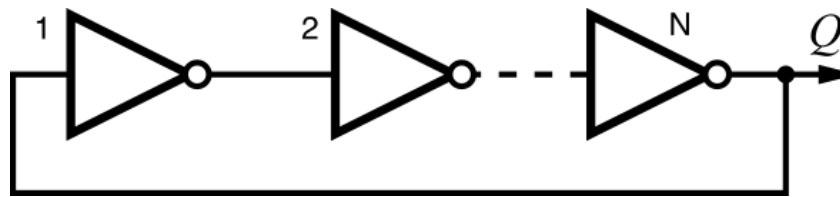
$$\sqrt{\frac{2}{K_n}} \left(1 - \frac{1}{\sqrt{K}}\right) = \sqrt{I} R_s$$

$$I = \frac{2}{K_n R_s^2} \left(1 - \frac{1}{\sqrt{K}}\right)^2$$



Q2.

Calculate the number of Inverters in the ring oscillator to achieve the frequency of 0.8 GHz, given the $T_{dHL}=20\text{pS}$, $T_{dLH}=30\text{pS}$. Also, can 1GHz be generated with given delay times?



$$\text{Timeperiod } T = N(T_{dHL} + T_{dLH}) = N \cdot 50\text{pS}$$

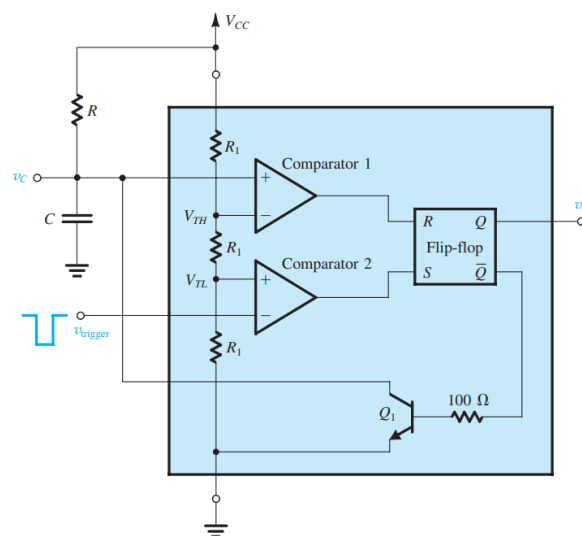
$$\Rightarrow 0.8\text{GHz} = 1/T = 1/(N \cdot 50\text{pS})$$

$$\Rightarrow N=25$$

For a frequency of 1GHz, N turns out to be 20. For N= even , the setup acts as a memory instead of oscillator , so cant generate 1GHz

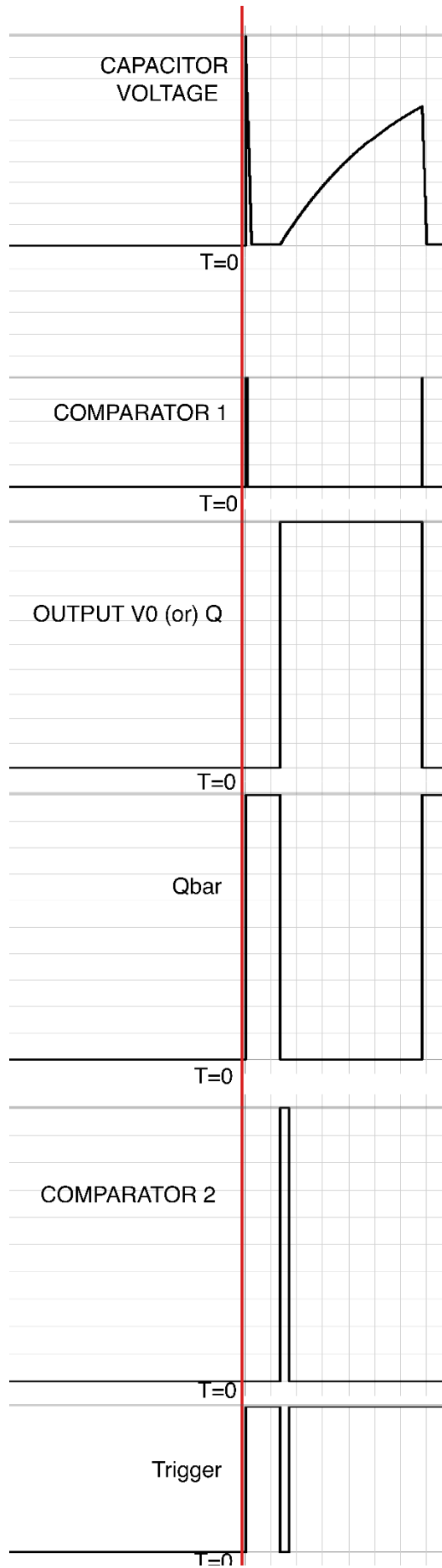
Q3.

Using a 10-nF capacitor C, find the value of R that yields an output pulse of 100 μs in the monostable circuit. Sketch the waveforms of V_C , V_O , V_{trigger} , the output of comparators, and RS flipflop, assuming that capacitance is initially charged to V_{CC} .



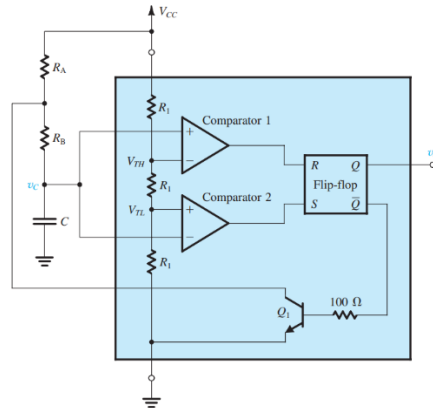
$$\text{Pulse duration} = \text{Capacitance charging time from } 0 \text{ v to } 2/3 V_{CC} = RC \ln(3)$$

$$\Rightarrow R = 100\mu / (10\text{n} \cdot \ln(3)) = 10 \cdot 1000 / \ln(3) = 9.1\text{Kohm}$$



Q4.

For the given circuit, find the values of R_A and R_B that result in an oscillation frequency of 100 kHz and a duty cycle of 75%, given $C = 1\text{ nF}$. Also, Sketch the waveforms of V_C , V_O



T_H = capacitance charging time from $1/3 V_{CC}$ to $2/3 V_{CC}$ through R_A and $R_B = C(R_A + R_B) \ln 2$

T_L = capacitance charging time from $2/3 V_{CC}$ to $1/3 V_{CC}$ through $R_B = C \cdot R_B \ln(2)$

Dutycycle = $T_H / (T_H + T_L) = [R_A + R_B] / [R_A + 2R_B] = 3/4$ (75%)

$\Rightarrow R_A = 2R_B$

For 75% dutycycle of 100Khz wave the $T_L = \frac{1}{4} \cdot 10 \mu\text{s}$

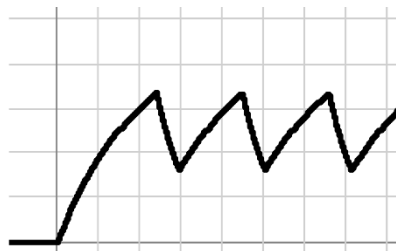
$\Rightarrow C \cdot R_B \cdot \ln(2) = 10/4 \mu$

$\Rightarrow 1\text{ n} \cdot R_B \cdot \ln(2) = 10/4 \mu$

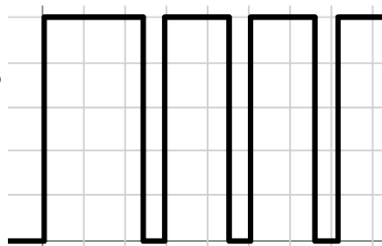
$\Rightarrow R_B = 10 \cdot 1000 / (4 \cdot \ln 2) = 3606.73 = 3.6 \text{ kohm}$

$R_A = 2 \cdot R_B = 7.2 \text{ kohm}$

Max = $2V_{DD}/3 \text{ V}$
Min = $V_{DD}/3 \text{ V}$
capacitor, 1 nF

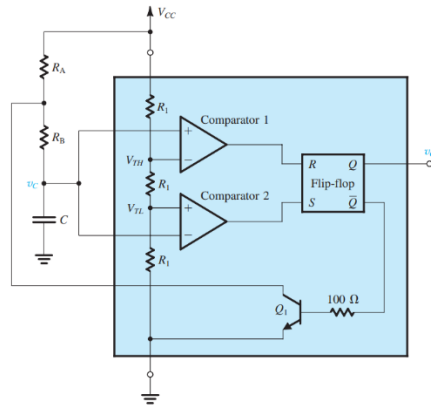


Max = V_{DD}
Duty cycle 75%
output



Q5

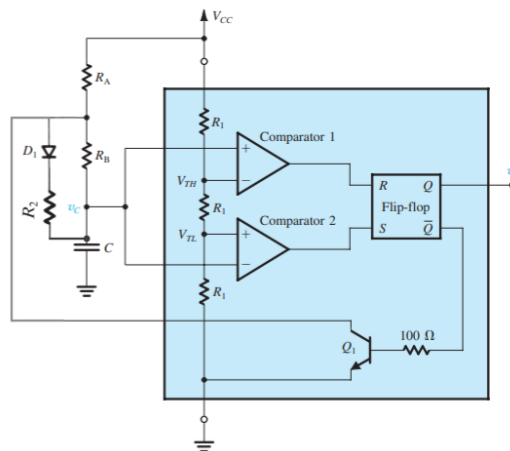
What is the minimum possible duty cycle with this configuration?



$$\text{Dutycycle} = \frac{TH}{TH+TL} = \frac{RA+RB}{RA+2RB}$$

Minimum possible duty cycle is 50% (when RA is much smaller than RB)

The following modification is made to the above circuit, Assume a diode is ideal, now derive the expression for the duty-cycle in terms of resistances RA, RB, R2.



During the charging process, the diode acts as short and RB is parallel to R2

Hence the charging process happens through $RA + (RB || R2)$

Discharge through RB , diode blocks current through R2

$$\text{So Dutycycle} = \frac{TH}{TH+TL} = \frac{RA+RB||R2}{RA+RB+RB||R2}$$

Note that this duty cycle has no min limit as before (by choosing large enough RB and small R2 one can less than 50% dutycycle)